

# E4MS015075J2

## Automotive Silicon Carbide Power MOSFET



### Features

- Industry compatible drive voltage 15 V ...18 V/-4 V ...0 V
- Soft body diode with low  $V_{DS}$  overshoot and ringing
- Low  $R_{DS(on)}$  at high operating temperatures
- Improved device capacitances ratio ( $C_{iss}/C_{rss}$ )
- High transient voltage robustness with improved lifetime
- Halogen free, RoHS compliant
- Automotive Qualified (AEC-Q101) and PPAP Capable

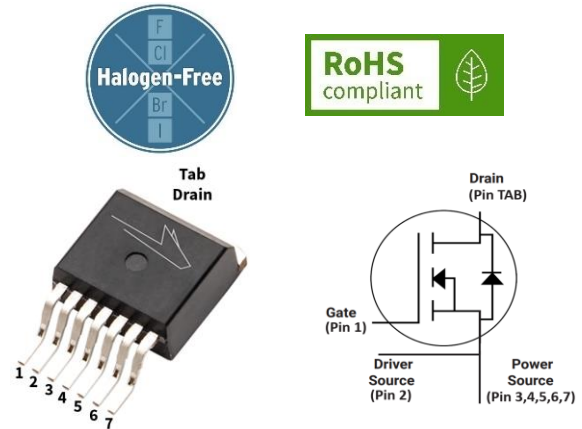
### Benefits

- Higher efficiency with lower switching losses and EMI
- Faster switching operation enabling high power density
- Enables system level price performance optimization
- Reduction in system level cooling requirements

### Typical Applications

- Onboard charger
- High voltage DC/DC converters
- HVAC compressors
- Battery management systems

### Package



Orderable Part Number	Package Type	Marking
E4MS015075J2-TR	TO-263-7XL	E4MS015075J2

### Absolute Maximum Ratings

Stress beyond those listed under absolute maximum ratings may damage the device.

Symbol	Parameter	Min.	Max.	Unit	Conditions	Note
$V_{DS(max)}$	Drain-Source Voltage		750	V		
$V_{GS(max)}$	Maximum Gate – Source Voltage (Transient)	-8	+23			Note 1
$I_D$	DC Continuous Drain Current		136	A	$V_{GS} = 18\text{ V}, T_c = 25\text{ }^\circ\text{C}, T_J \leq 175\text{ }^\circ\text{C}$	Note 2
			95		$V_{GS} = 18\text{ V}, T_c = 100\text{ }^\circ\text{C}, T_J \leq 175\text{ }^\circ\text{C}$	
$I_{DM}$	Pulsed Drain Current		319		$V_{GS} = 18\text{ V}, T_c = 25\text{ }^\circ\text{C}, t_{Pmax}$ limited by $T_{Jmax}$	
$P_D$	Power Dissipation		433	W	$T_c = 25\text{ }^\circ\text{C}, T_J = 175\text{ }^\circ\text{C}$	Note 3
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-55	+175	$^\circ\text{C}$		
$T_L$	Solder Temperature		260		According to JEDEC J-STD-020	

Note (1): Refer to AN PRD-09634

Note (2): Current limit calculated by  $I_{D(max)} = \sqrt{(P_D / R_{DS(typ)}) / (T_J(max), D(max))}$

Note (3):  $P_D = (T_J - T_c) / R_{th(JC,Max)}$



## Electrical Characteristics ( $T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain – Source Breakdown Voltage	750			V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2	2.6	3.9	V	$V_{DS} = V_{GS}, I_D = 12.55\ \text{mA}$	Fig. 11, Note 1
			2		V	$V_{DS} = V_{GS}, I_D = 12.55\ \text{mA}, T_J = 175^\circ\text{C}$	
$I_{DSS}$	Zero Gate Voltage Drain Current		1	50	$\mu\text{A}$	$V_{DS} = 750\ \text{V}, V_{GS} = 0\ \text{V}$	
$I_{GSS}$	Gate-Source Leakage Current		10	250	nA	$V_{GS} = 18\ \text{V}, V_{DS} = 0\ \text{V}$	
$V_{GS(op)}$	Recommended Turn on Gate-Source Voltage		+15...+18		V		Note 4
	Recommended Turn off Gate-Source Voltage		-4...0				
$R_{DS(on)}$	Drain-Source On-State Resistance		15	19.5	m $\Omega$	$V_{GS} = 18\ \text{V}, I_D = 45.6\ \text{A}$	Fig. 4, 5, 6
			22			$V_{GS} = 18\ \text{V}, I_D = 45.6\ \text{A}, T_J = 175^\circ\text{C}$	
			18			$V_{GS} = 15\ \text{V}, I_D = 45.6\ \text{A}$	
$g_{fs}$	Transconductance		33		S	$V_{DS} = 20\ \text{V}, I_D = 45.6\ \text{A}$	Fig. 7
			34			$V_{DS} = 20\ \text{V}, I_D = 45.6\ \text{A}, T_J = 175^\circ\text{C}$	
$R_{DS(on)Tempco}$	On resistance temperature coefficient		1.47			$V_{GS} = 18\ \text{V}, I_D = 45.6\ \text{A}$	Note 5
$C_{iss}$	Input Capacitance		3748		pF	$V_{GS} = 0\ \text{V}, V_{DS} = 500\ \text{V}$ $f = 100\ \text{kHz}$ $V_{AC} = 25\ \text{mV}$	Fig. 17, 18
$C_{oss}$	Output Capacitance		218				
$C_{rss}$	Reverse Transfer Capacitance		8				
$E_{oss}$	$C_{oss}$ Stored Energy		35.7				$\mu\text{J}$
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		280		pF	$V_{GS} = 0\ \text{V}, V_{DS} = 0\ \text{V} \dots 500\ \text{V}$	Note 6
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		445				
$E_{on}$	Turn-On Switching Energy (Body Diode FWD) $T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$		201		$\mu\text{J}$	$V_{DS} = 500\ \text{V}, V_{GS} = -4\ \text{V} / 18\ \text{V},$ $I_D = 45.6\ \text{A}, R_{G(ext)} = 2\ \Omega, L_\sigma = 25\ \text{nH}$	Fig. 25, 27, 29
			203				
$E_{off}$	Turn-Off Switching Energy (Body Diode FWD) $T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$		70				Fig. 25, 28, 29
			71				
$t_{d(on)}$	Turn-On Delay Time		12.9		ns	$V_{DS} = 500\ \text{V}, V_{GS} = -4\ \text{V} / 18\ \text{V},$ $I_D = 45.6\ \text{A}, R_{G(ext)} = 2\ \Omega, L_\sigma = 25\ \text{nH}$	Fig. 26, 27, 29
$t_r$	Rise Time		5.2				
$t_{d(off)}$	Turn-Off Delay Time		40.2				Fig. 26, 28, 29
$t_f$	Fall Time		9.8				
$R_{G(int)}$	Internal Gate Resistance		2.2		$\Omega$	$f = 1\ \text{MHz}$	
$Q_{gs}$	Gate to Source Charge		41		nC	$V_{DS} = 500\ \text{V}, V_{GS} = -4\ \text{V} / 18\ \text{V}$ $I_D = 45.6\ \text{A}$	Fig. 12
$Q_{gd}$	Gate to Drain Charge		43				
$Q_g$	Total Gate Charge		147				

Note (4): Refer to AN PRD-08999.

Note (5):  $R_{DS(on)Tempco}$  refers to  $R_{DS(on)}$  at  $25^\circ\text{C}$  /  $R_{DS(on)}$  at  $175^\circ\text{C}$ . This is a E4MS 750 V product family value.

Note (6):  $C_{o(er)}$ , a lumped capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 500 V.

$C_{o(tr)}$ , a lumped capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 500 V.



### Reverse Diode Characteristics ( $T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_{SD}$	Diode Forward Voltage	5.1		V	$V_{GS} = -4\text{ V}, I_{SD} = 22.8\text{ A}, T_J = 25\text{ }^\circ\text{C}$	Fig. 8, 9, 10
		4.5			$V_{GS} = -4\text{ V}, I_{SD} = 22.8\text{ A}, T_J = 175\text{ }^\circ\text{C}$	
$I_S$	Continuous Diode Forward Voltage		70	A	$V_{GS} = -4\text{ V}, T_c = 25\text{ }^\circ\text{C}$	
$I_{SM}$	Diode Pulse Current		319		$V_{GS} = -4\text{ V}$ , pulse width $t_p$ limited by $T_{jmax}$	
$t_{rr}$	Reverse Recovery Time	10.6		ns	$V_{GS} = -4\text{ V}, I_{SD} = 45.6\text{ A}, V_R = 500\text{ V}$ , $di/dt = 11288\text{ A}/\mu\text{s}, T_J = 175\text{ }^\circ\text{C}$ , $R_{G(ext)} = 2\text{ }\Omega, L_G = 25\text{ nH}$	Fig. 30
$Q_{rr}$	Reverse Recovery Charge	467.5		nC		
$I_{RRM}$	Peak Reverse Recovery Current	75		A		
$E_{RR}$	Reverse Recovery Energy $T_j = 25\text{ }^\circ\text{C}$ $T_j = 175\text{ }^\circ\text{C}$	160 170		$\mu\text{J}$		

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.3	0.39	K/W		



Typical Performance

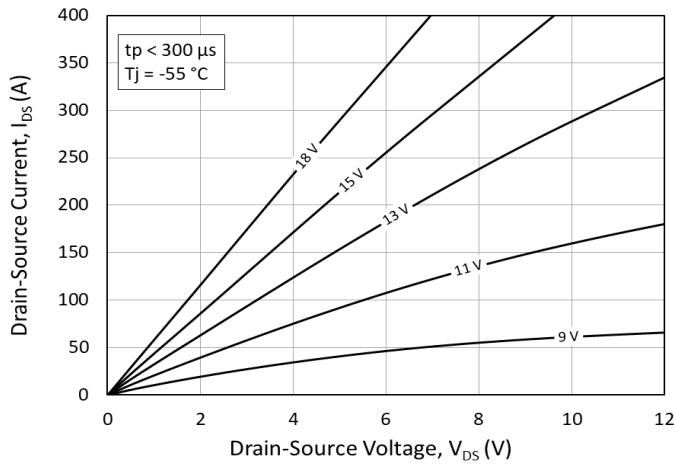


Figure 1. Output Characteristics  $T_{vj} = -55\text{ }^{\circ}\text{C}$

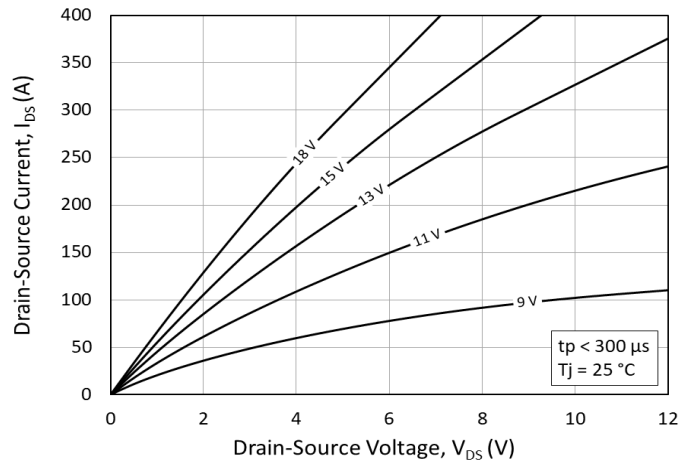


Figure 2. Output Characteristics  $T_{vj} = 25\text{ }^{\circ}\text{C}$

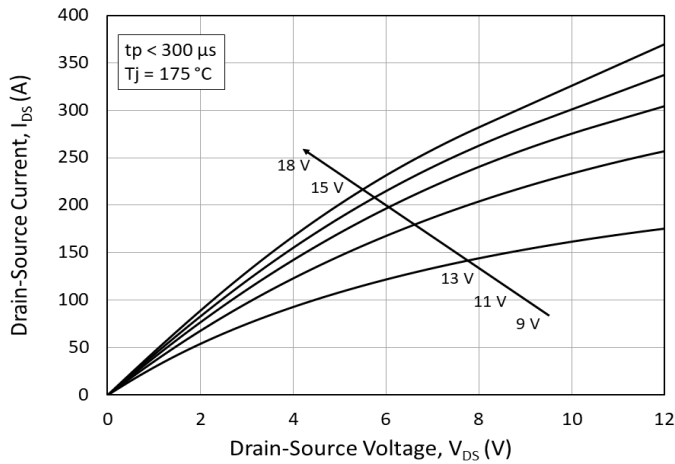


Figure 3. Output Characteristics  $T_{vj} = 175\text{ }^{\circ}\text{C}$

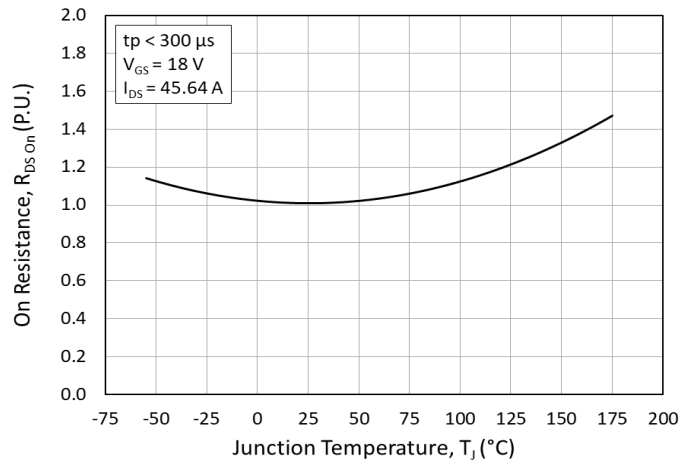


Figure 4. Normalized On-Resistance vs. Temperature

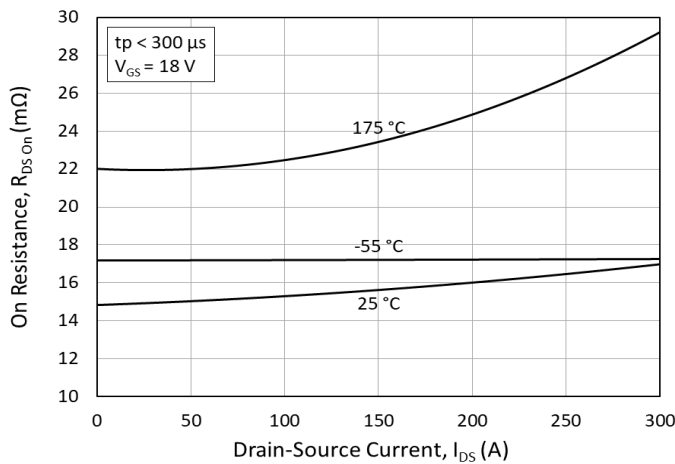


Figure 5. On-Resistance vs. Drain Current for Various Temperatures

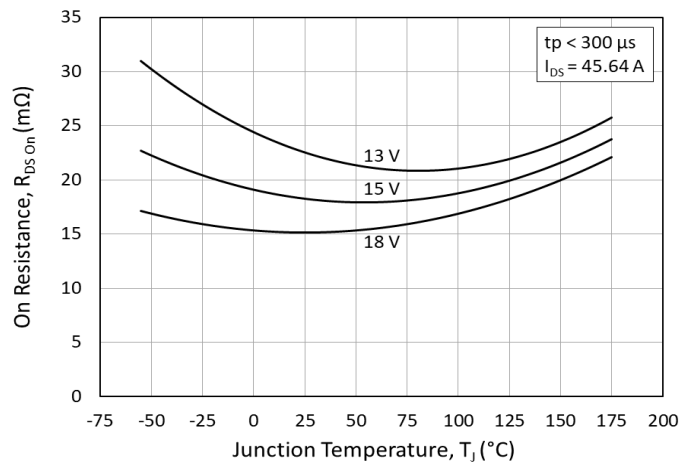


Figure 6. On-Resistance vs. Temperature for Various Gate Voltages



Typical Performance

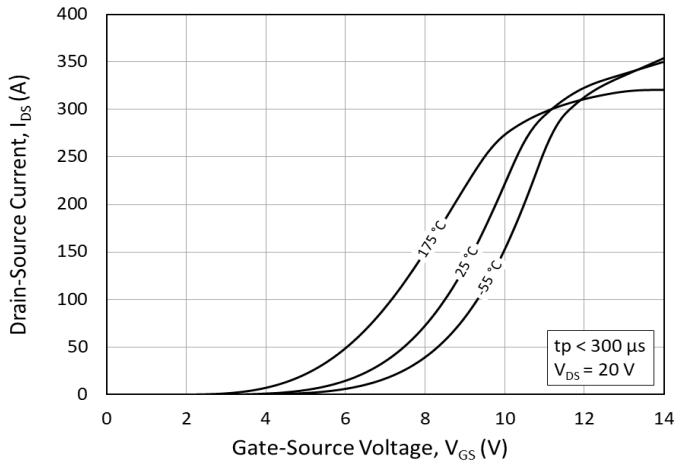


Figure 7. Transfer Characteristic for Various Junction Temperatures

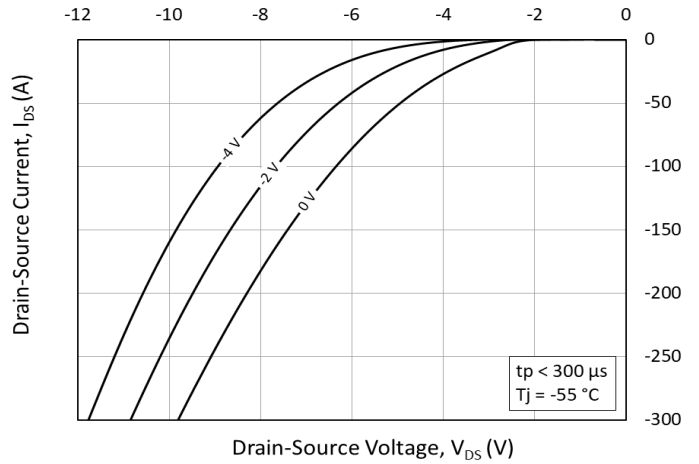


Figure 8. Body Diode Characteristic at  $T_{J} = -55\text{ }^{\circ}\text{C}$

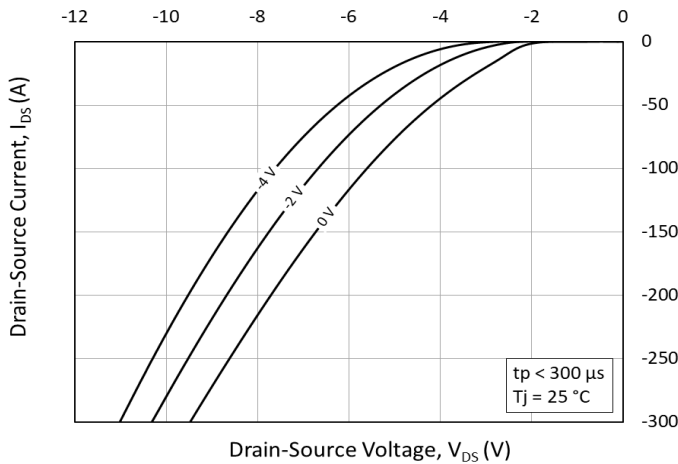


Figure 9. Body Diode Characteristic at  $T_{J} = 25\text{ }^{\circ}\text{C}$

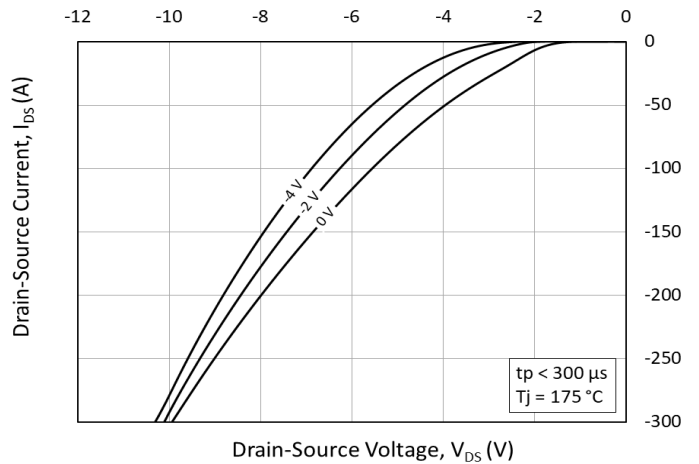


Figure 10. Body Diode Characteristic at  $T_{J} = 175\text{ }^{\circ}\text{C}$

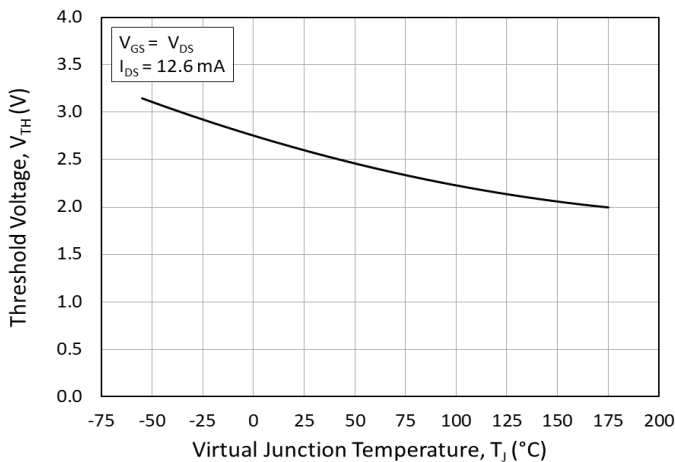


Figure 11. Threshold Voltage vs. Temperature

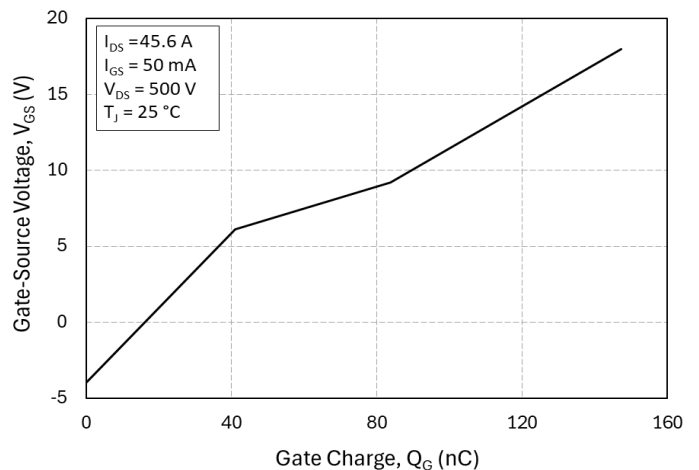


Figure 12. Gate Charge Characteristics



Typical Performance

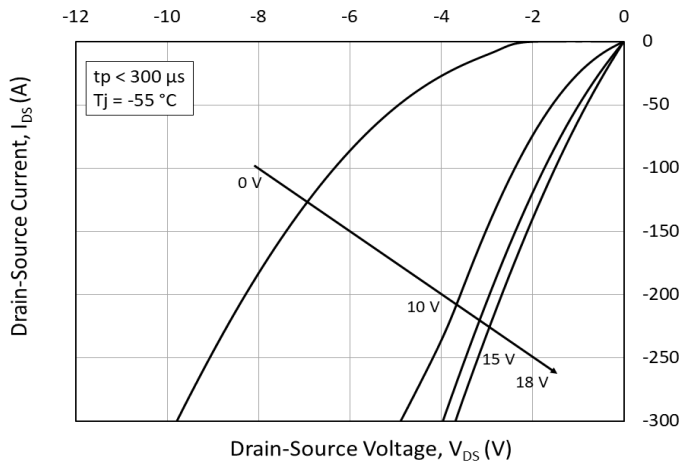


Figure 13. 3rd Quadrant Characteristic at  $T_{VJ} = -55\text{ }^{\circ}\text{C}$

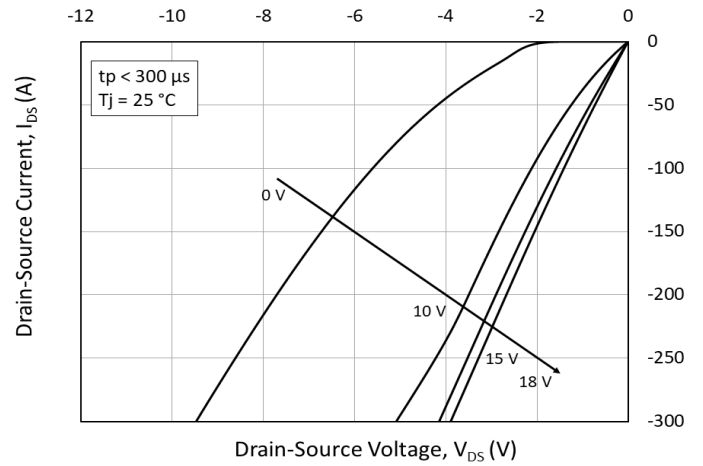


Figure 14. 3rd Quadrant Characteristic at  $T_{VJ} = 25\text{ }^{\circ}\text{C}$

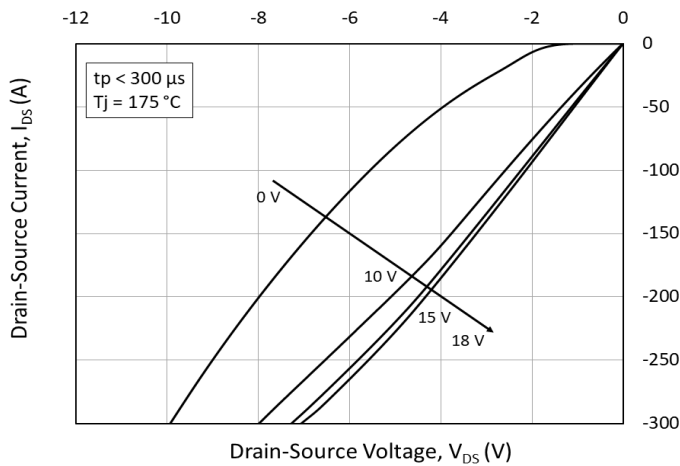


Figure 15. 3rd Quadrant Characteristic at  $T_{VJ} = 175\text{ }^{\circ}\text{C}$

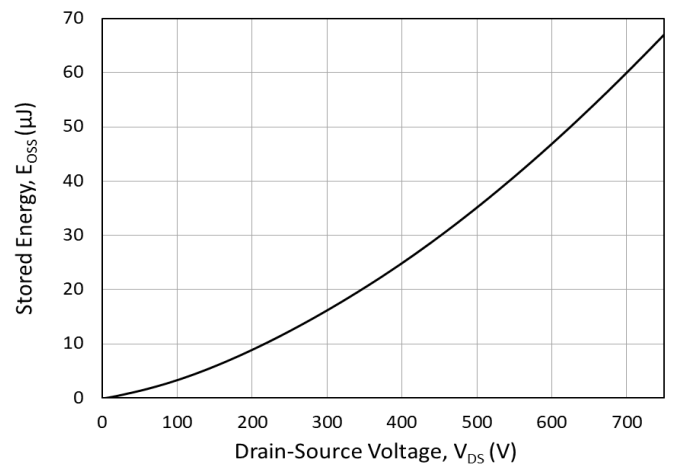


Figure 16. Output Capacitor Stored Energy

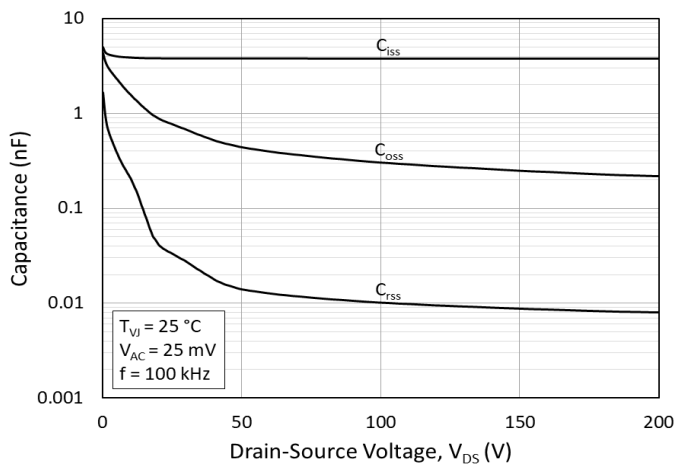


Figure 17. Capacitances vs. Drain-Source Voltage (0-200 V)

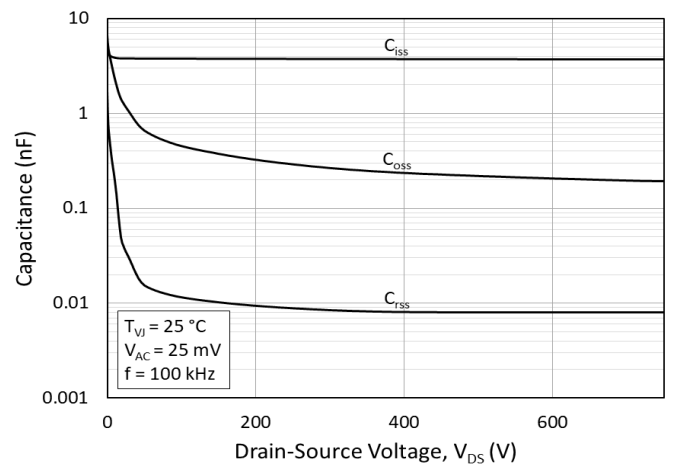


Figure 18. Capacitances vs. Drain-Source Voltage (0-750 V)



Typical Performance

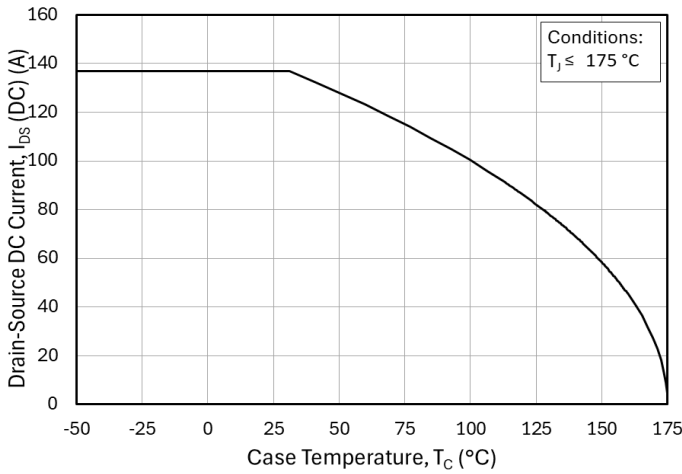


Figure 19. Continuous Drain Current Derating vs. Case Temperature

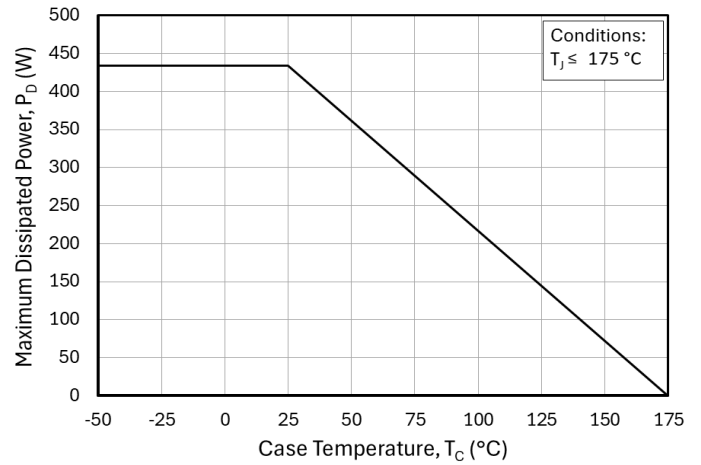


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

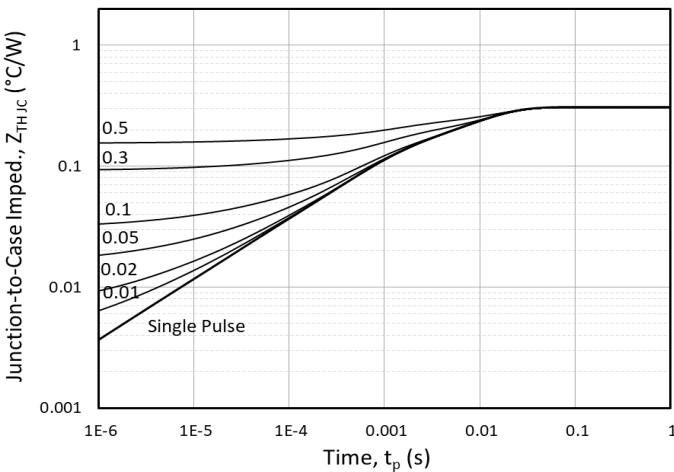


Figure 21. Transient Thermal Impedance (Junction - Case) °C/W

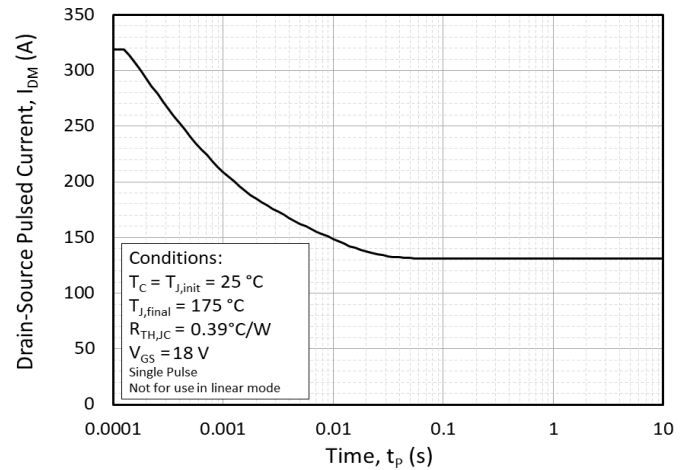


Figure 22. Safe Operating Area

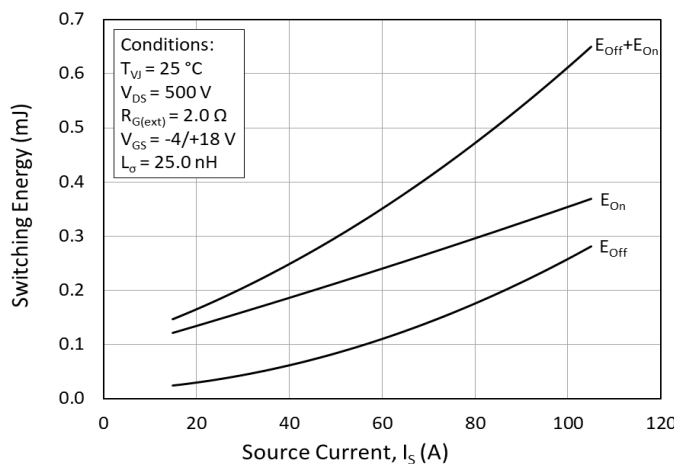


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 500\text{ V}$ )

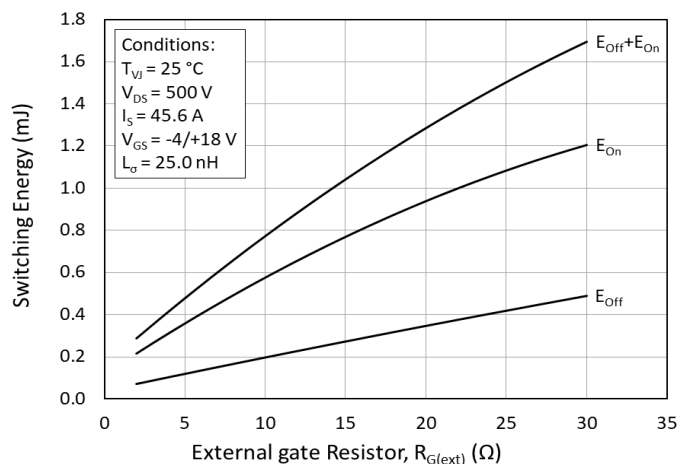


Figure 24. Clamped Inductive Switching Energy vs.  $R_{G(ext)}$

Typical Performance

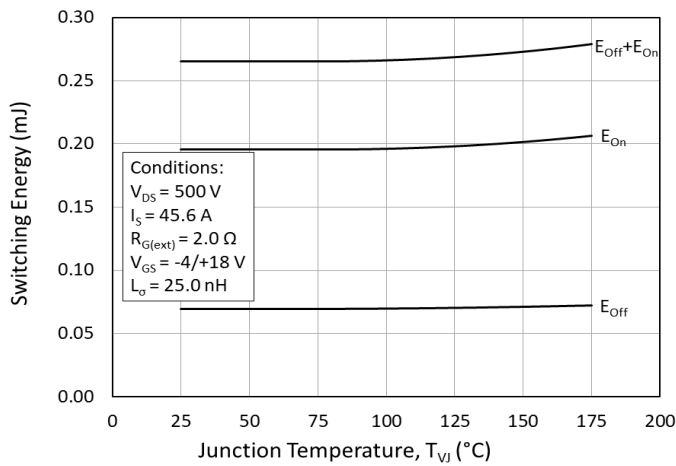


Figure 25. Clamped Inductive Switching Energy vs. Temperature

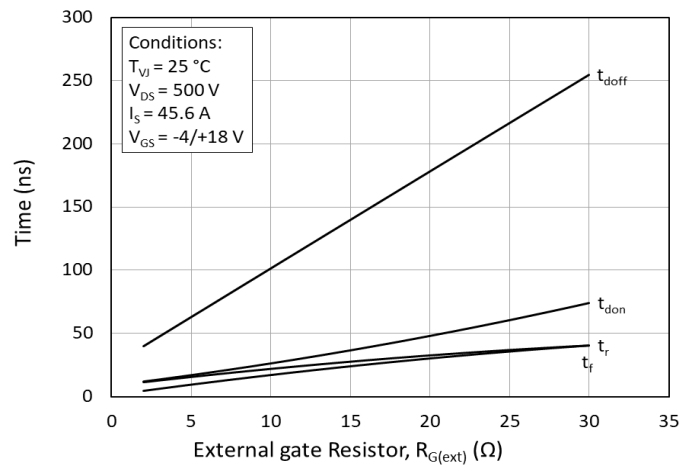


Figure 26. Switching Times vs.  $R_{G(ext)}$

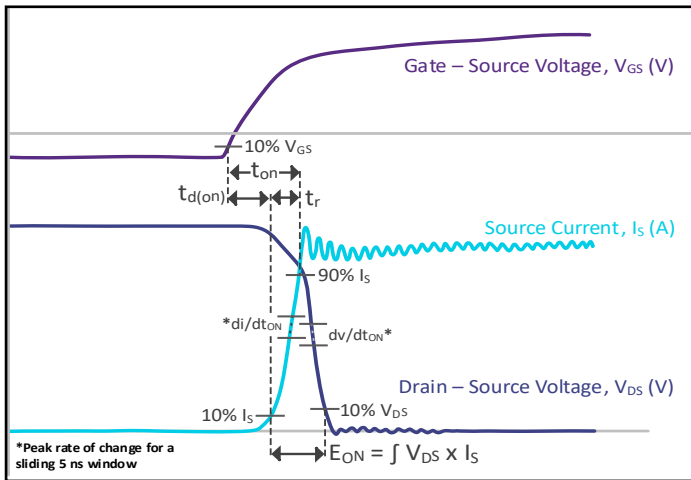


Figure 27. Turn On Switching Time Definition

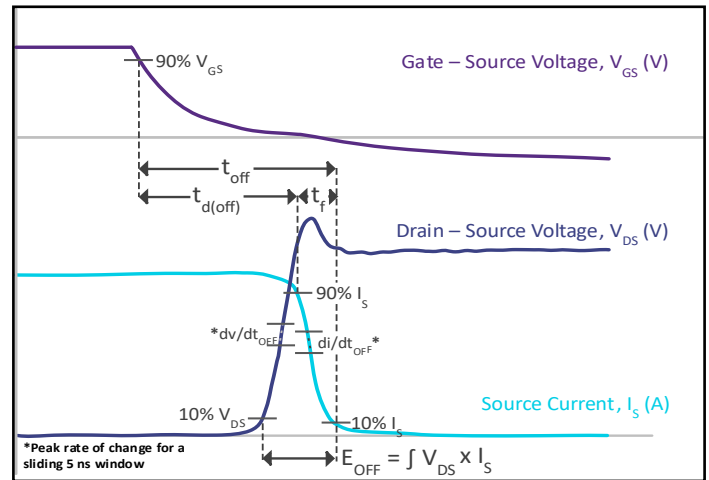


Figure 28. Turn Off Switching Time Definition

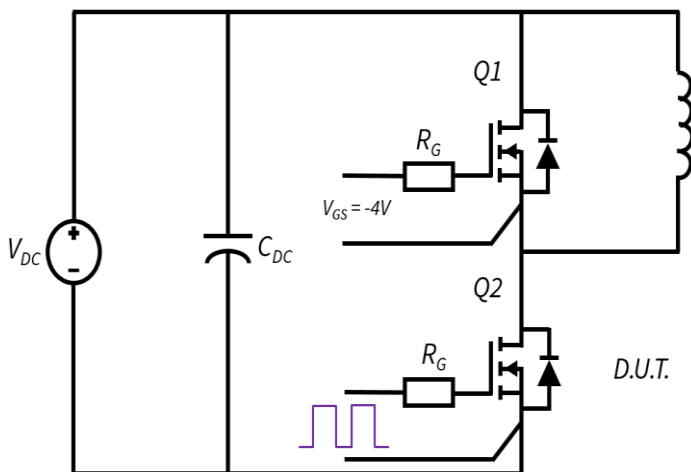


Figure 29. Clamped Inductive MOSFET Switching Waveform Test Circuit

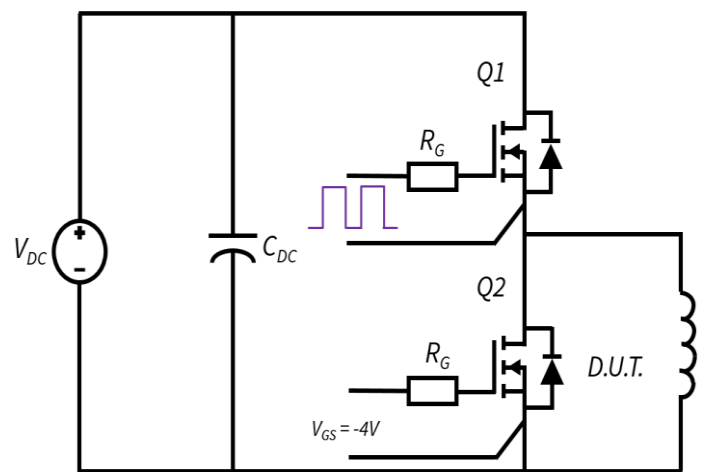
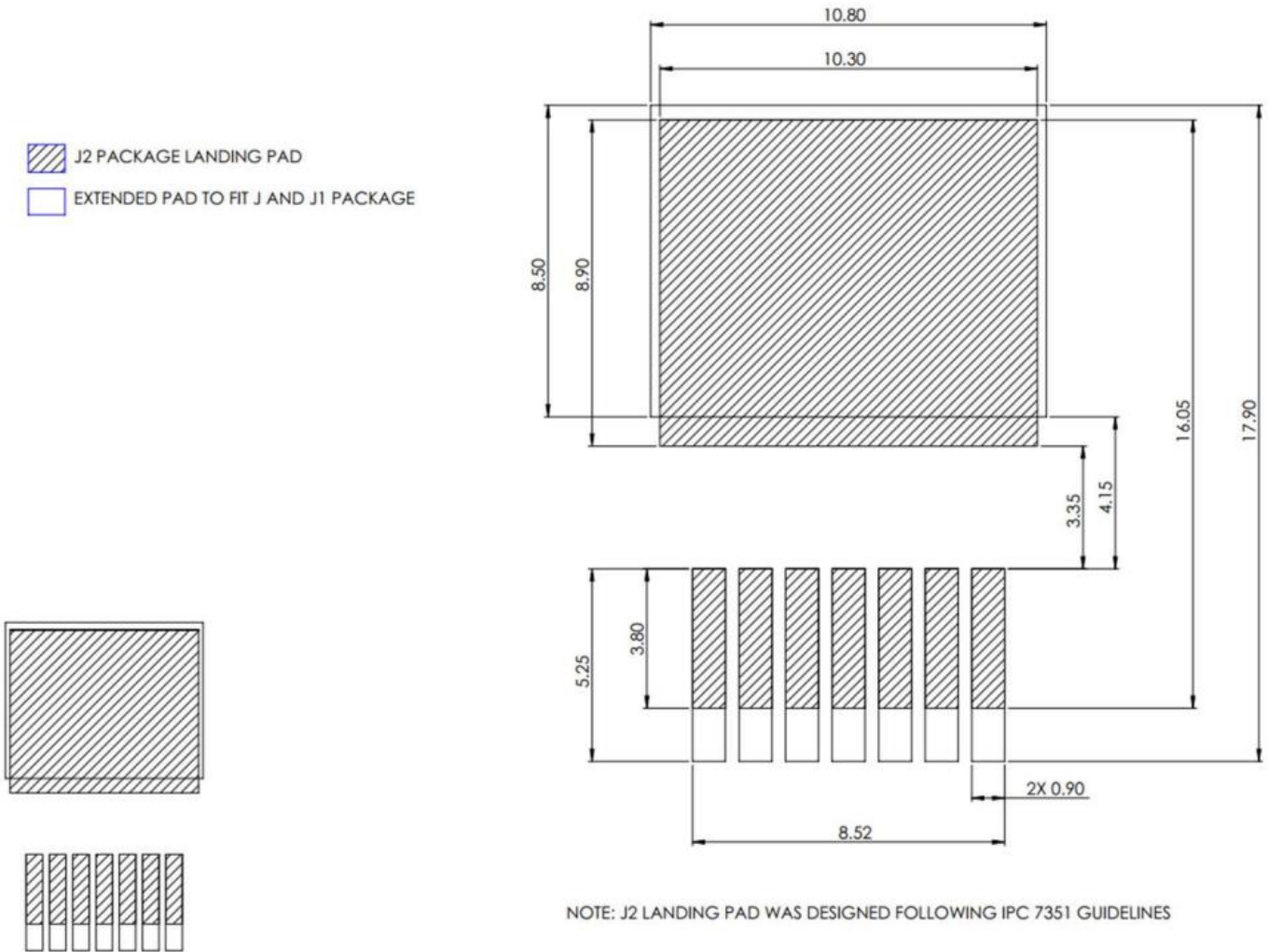


Figure 30. Clamped Inductive Body Diode Switching Waveform Test Circuit



### Recommended Solder Pad Layout

All dimensions in mm





## Revision History

Documents Version	Date of Change	Description of Changes
1	April 2026	Initial Release

## Appendix

Appendix Number	Description
A1	<p>The following are recommendations for turning off the MOSFET with 0 V:</p> <ul style="list-style-type: none"><li>• Measure the <math>V_{GS}</math> spike accurately using high-CMRR probes and low common mode noise measurements.</li><li>• For the safe operation of the device, the voltage spike shall remain &lt; 5V for a time duration of &lt; 40 ns.</li></ul>



## Notes & Disclaimers

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